

N-channel LFPAK 80 V 45 mΩ standard level MOSFET

Rev. 02 — 25 October 2010

Product data sheet

#### 1. **Product profile**

### 1.1 General description

Standard level N-channel MOSFET in LFPAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

### 1.2 Features and benefits

- Advanced TrenchMOS provides low RDSon and low gate charge
- High efficiency gains in switching power converters

### 1.3 Applications

- DC-to-DC converters
- Lithium-ion battery protection
- Load switching

### Improved mechanical and thermal characteristics

- LFPAK provides maximum power density in a Power SO8 package
- Motor control
- Server power supplies

### 1.4 Quick reference data

Table 1.	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	-	80	V
I <sub>D</sub>	drain current	$T_{mb} = 25 \text{ °C}; V_{GS} = 10 \text{ V}$	-	-	24	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	-	56	W
Tj	junction temperature		-55	-	175	°C
Static cha	aracteristics					
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 5 \text{ A};$ T <sub>j</sub> = 100 °C; see <u>Figure 13</u>	-	-	72	mΩ
		$V_{GS}$ = 10 V; $I_{D}$ = 5 A; $T_{j}$ = 25 °C	-	37	45	mΩ

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### N-channel LFPAK 80 V 45 mΩ standard level MOSFET

Table 1.         Quick reference data continued						
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Dynamic	characteristics					
$Q_{GD}$	gate-drain charge	$V_{GS} = 10 \text{ V}; \text{ I}_{D} = 15 \text{ A};$	-	3.1	-	nC
Q <sub>G(tot)</sub>	total gate charge	V <sub>DS</sub> = 40 V; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	12.5	-	nC
Avalanche ruggedness						
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$ \begin{array}{l} V_{GS} = 10 \; V; \; T_{j(init)} = 25 \; ^{\circ}C; \\ I_{D} = 22 \; A; \; V_{sup} \leq 80 \; V; \\ R_{GS} = 50 \; \Omega; \; unclamped \end{array} $	-	-	18	mJ

### 2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		_
2	S	source	mb	
3	S	source		
4	G	gate		
mb	D	mounting base; connected to drain		mbb076 S
			SOT669 (LFPAK)	

### 3. Ordering information

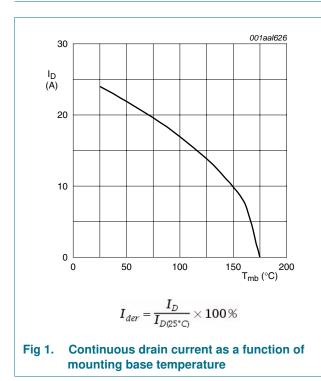
Table 3.	Ordering in	formation		
Type num	ber	Package		
		Name	Description	Version
PSMN045-	80YS	LFPAK	plastic single-ended surface-mounted package (LFPAK); 4 leads	SOT669

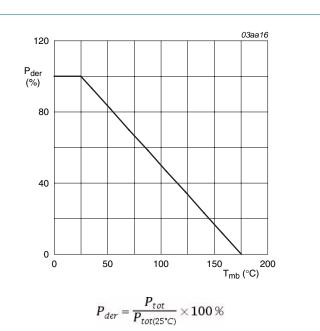
### 4. Limiting values

#### Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

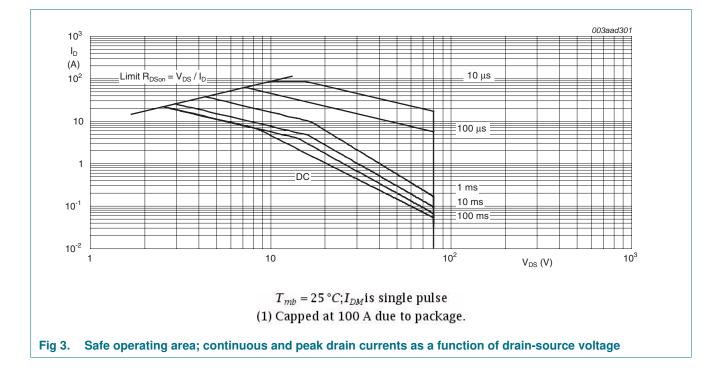
Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	80	V
V <sub>DGR</sub>	drain-gate voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C; R <sub>GS</sub> = 20 kΩ	-	80	V
V <sub>GS</sub>	gate-source voltage		-20	20	V
I <sub>D</sub>	drain current	$V_{GS}$ = 10 V; $T_{mb}$ = 100 °C; see <u>Figure 1</u>	-	17	А
		$V_{GS} = 10 \text{ V}; \text{ T}_{mb} = 25 \text{ °C}$	-	24	А
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$ ; see Figure 3	-	86	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	56	W
T <sub>stg</sub>	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
$T_{sld(M)}$	peak soldering temperature		-	260	°C
Source-drai	n diode				
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	-	24	А
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$	-	86	А
Avalanche r	ruggedness				
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 22 A; $V_{sup} \le 80$ V; $R_{GS}$ = 50 $\Omega$ ; unclamped	-	18	mJ





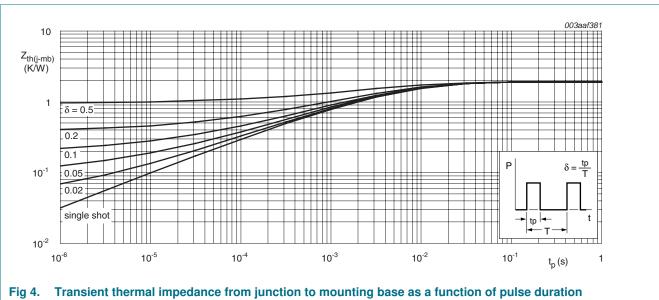


### **PSMN045-80YS**



#### **Thermal characteristics** 5.

Table 5.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	see Figure 4	-	1.9	2.7	K/W



### 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara		Conditions	IVIIII	тур	Max	Unit
			73			V
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$I_D = 250 \ \mu\text{A}; \ V_{GS} = 0 \ \text{V}; \ T_j = -55 \ \text{°C}$		-	-	-
.,		$I_D = 250 \ \mu A; V_{GS} = 0 \ V; T_j = 25 \ ^{\circ}C$	80	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ see <u>Figure 11</u> ; see <u>Figure 12</u>	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ see <u>Figure 11</u> ; see <u>Figure 12</u>	-	-	4.6	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 12</u> ; see <u>Figure 11</u>	2	3	4	V
IDSS	drain leakage current	$V_{DS} = 80 \text{ V}; \text{ V}_{GS} = 0 \text{ V}; \text{ T}_{j} = 25 \text{ °C}$	-	-	1	μA
		V <sub>DS</sub> = 80 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 125 °C	-	-	50	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_{j} = 25 \text{ °C}$	-	-	100	nA
		$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nA
R <sub>DSon</sub> drain-source on-state resistance		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 5 A; T <sub>j</sub> = 175 °C; see <u>Figure 13</u>	-	-	103	mΩ
		$V_{GS} = 10 \text{ V}; \text{ I}_{D} = 5 \text{ A}; \text{ T}_{j} = 100 \text{ °C};$ see Figure 13	-	-	72	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 5 A; T <sub>i</sub> = 25 °C	-	37	45	mΩ
R <sub>G</sub>	internal gate resistance (AC)	f = 1 MHz	-	0.73	-	Ω
Dynamic cł	naracteristics					
Q <sub>G(tot)</sub> total gate charge		I <sub>D</sub> = 0 A; V <sub>DS</sub> = 0 V; V <sub>GS</sub> = 10 V	-	9	-	nC
6((6))		$I_D = 15 \text{ A}; V_{DS} = 40 \text{ V}; V_{GS} = 10 \text{ V};$	-	12.5	-	nC
Q <sub>GS</sub>	gate-source charge	see Figure 14; see Figure 15	-	3.8	_	nC
Q <sub>GS(th)</sub>	pre-threshold gate-source charge		-	1.9	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate-source charge	$I_D = 15 \text{ A}; V_{DS} = 40 \text{ V}; V_{GS} = 10 \text{ V};$ see Figure 14	-	1.9	-	nC
Q <sub>GD</sub>	gate-drain charge	$I_D = 15 \text{ A}; V_{DS} = 40 \text{ V}; V_{GS} = 10 \text{ V};$ see Figure 14; see Figure 15	-	3.1	-	nC
V <sub>GS(pl)</sub>	gate-source plateau voltage	$I_D = 15 \text{ A}; V_{DS} = 40 \text{ V}; \text{ see Figure 14}$	-	4.9	-	V
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 40 V; V <sub>GS</sub> = 0 V; f = 1 MHz;	-	675	-	pF
C <sub>oss</sub>	output capacitance	$T_j = 25 \text{ °C}; \text{ see } Figure 17$	-	79	-	pF
Crss	reverse transfer capacitance		-	48	-	pF
- 133 d(on)	turn-on delay time	$V_{DS} = 40 \text{ V}; \text{ R}_{L} = 2.7 \Omega; \text{ V}_{GS} = 10 \text{ V};$	-	9.2	-	ns
	rise time	$R_{G(ext)} = 4.7 \Omega$	-	4.6	-	ns
d(off)	turn-off delay time		-	18	-	ns
t <sub>f</sub>	fall time		_	4.4	-	ns

Symbol

Source-drain diode

## **PSMN045-80YS**

Мах

Unit

Тур

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Min

V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 15 A; V <sub>GS</sub> see <u>Figure 16</u>	$_{s} = 0 V; T_{j} = 25 °C;$	-	0.82	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S = 5 \text{ A}; \text{ dI}_S/\text{d}$	t = 100 A/μs;	-	32	-	ns
Qr	recovered charge	$V_{GS} = 0 V; V_D$	<sub>S</sub> = 40 V	-	42	-	nC
40   <sub>D</sub> (A) 30 20 10		$v_{DS}(V)^{10}$	$ \begin{array}{c} 100 \\ R_{DSon} \\ (m\Omega) \\ 80 \\ 60 \\ 40 \\ 20 \\ 0 \\ 10 \end{array} $	5	5.5	003aad047 6 10 20 I <sub>D</sub> (A) 40	
	$T_j = 25 ^{\circ}C; t_p = 300 \mu s$ Dutput characteristics: drain c unction of drain-source voltag		$T_j = 2$ Fig 6. Drain-source or of drain current		esistanc	e as a fi	unctior
1000 C (pF) 800	-C <sub>iss</sub>	003aad052	9 <sup>35</sup> (S) 30 25 20			003aad053	
400	-C <sub>rss</sub>		15				
200							
0	2 4 6 8,	V <sub>GS</sub> (V) <sup>10</sup>	0 10 2	20 30	) 40	I <sub>D</sub> (A) 50	
	$V_{DS} = 0V; f = 1MHz$		$T_{\rm c} = 2$	5°C;V <sub>DS</sub>	- 151/		

Conditions

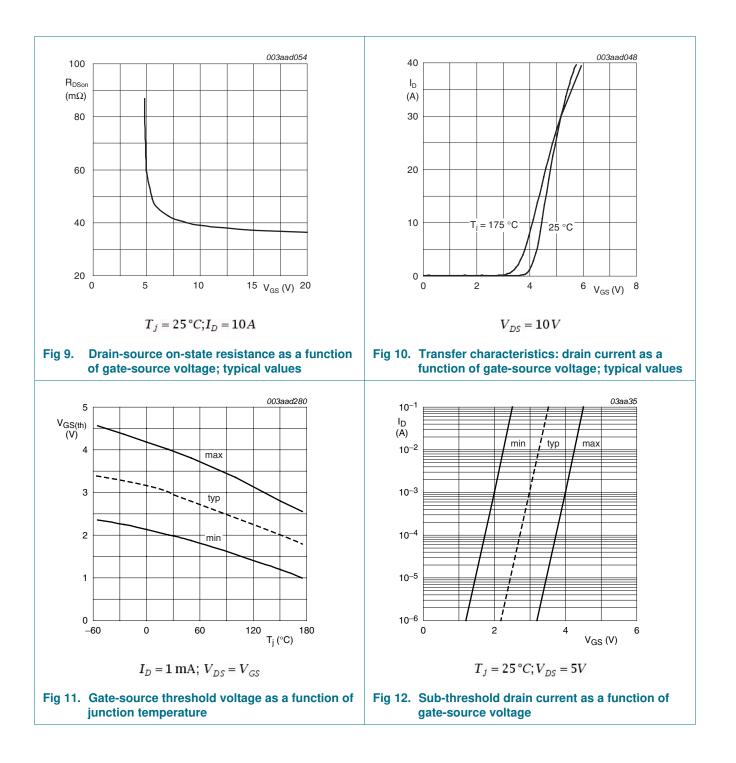
#### Table 6. Characteristics ... continued

Parameter

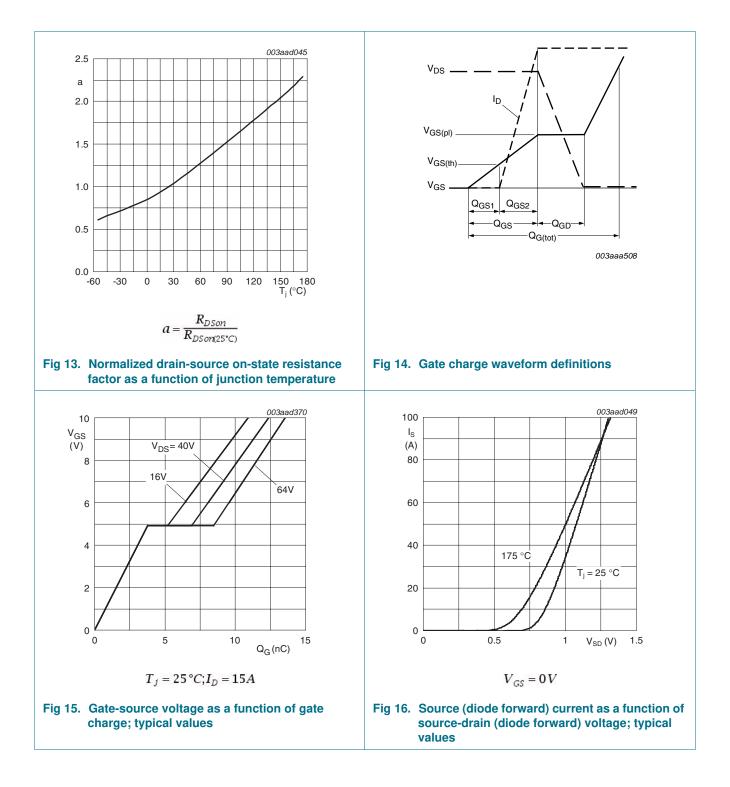
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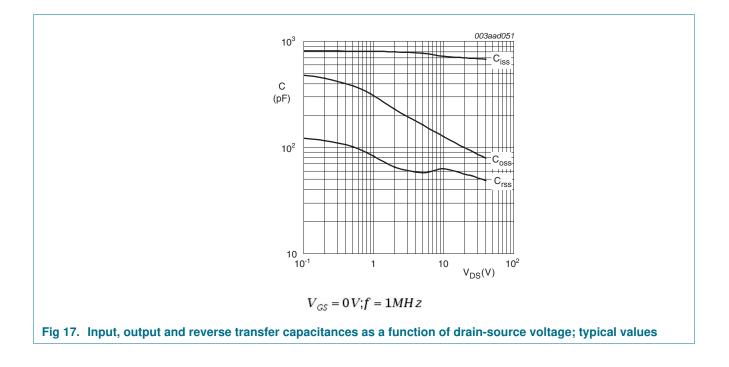
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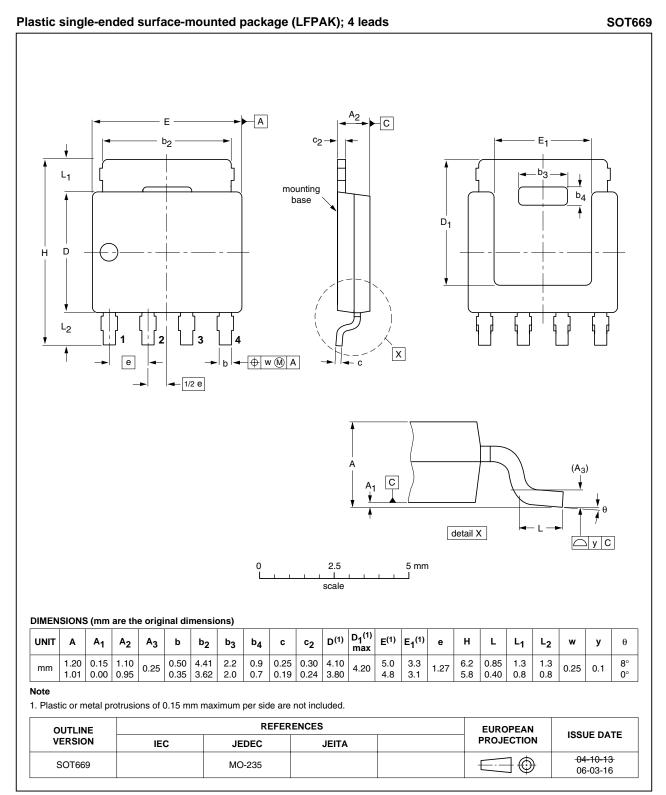


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### 7. Package outline



#### Fig 18. Package outline SOT669 (LFPAK)

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PSMN045-80YS

### 8. Revision history

Table 7. Revision h	nistory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN045-80YS v.2	20101025	Product data sheet	-	PSMN045-80YS v.1
Modifications:	<ul><li>Status change</li><li>Various chang</li></ul>	d from objective to product. es to content.		
PSMN045-80YS v.1	20100319	Objective data sheet	-	-

### 9. Legal information

### 9.1 Data sheet status

Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <u>http://www.nexperia</u>.com.

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